

# MJ N-Channel Enhancement Mode Power MOSFET

## Description

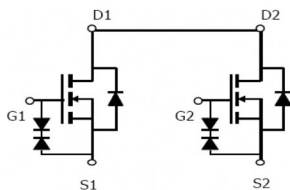
The MJ2010E uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications .It is ESD protested.

## General Features

- ◆  $V_{DS} = 20V, I_D = 7A$   
 $R_{DS(ON)} < 24m\Omega @ V_{GS} = 2.5V$   
 $R_{DS(ON)} < 18m\Omega @ V_{GS} = 4.5V$   
ESD Rating: 2000V HBM
- ◆ High power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

## Application

- ◆ PWM application
- ◆ Load switch



Schematic diagram



Marking and pin Assignment



TSSOP-8 top view

## Package Marking and Ordering Information

| Device Marking | Device  | Device Package | Reel Size | Tape width | Quantity   |
|----------------|---------|----------------|-----------|------------|------------|
| 2010E          | MJ2010E | TSSOP-8        | Ø330mm    | 12mm       | 3000 units |

## Absolute Maximum Ratings (Tc =25 °Cunless otherwise noted)

| Parameter  | Symbol         | Limit      | Unit |
|--|----------------|------------|------|
| Drain-Source Voltage                             | $V_{DS}$       | 20         | V    |
| Gate-Source Voltage                              | $V_{GS}$       | ±12        | V    |
| Drain Current-Continuous                         | $I_D$          | 7          | A    |
| Pulsed Drain Current <sup>(Note 1)</sup>         | $I_{DM}$       | 30         | A    |
| Maximum Power Dissipation                        | $P_D$          | 1.5        | W    |
| Operating Junction and Storage Temperature Range | $T_J, T_{STG}$ | -55 To 150 | °C   |

## Thermal Characteristic

|  |                 |      |      |
|--|-----------------|------|------|
| Thermal Resistance,Junction-to-Ambient <sup>(Note 2)</sup> | $R_{\theta JA}$ | 83.3 | °C/W |
|--|-----------------|------|------|

Electrical Characteristics (T<sub>A</sub> =25℃unless otherwise noted)

| Parameter                                     | Symbol              | Condition  | Min | Typ  | Max | Unit |
|---|---------------------|--|-----|------|-----|------|
| Off Characteristics                           |                     |  |     |      |     |      |
| Drain-Source Breakdown Voltage                | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =250μA  | 20  | 21.5 | 23  | V    |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> =20V,V <sub>GS</sub> =0V   | -   | -    | 1   | μA   |
| Gate-Body Leakage Current                     | I <sub>GSS</sub>    | V <sub>DS</sub> =±10V,V <sub>DS</sub> =0V  | -   | -    | ±10 | nA   |
| On Characteristics <sup>(Note 3)</sup>        |                     |  |     |      |     |      |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA                                | 0.5 | 0.7  | 0.9 | V    |
| Drain-Source On-State Resistance              | R <sub>DS(ON)</sub> | V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.5A  | -   | 13   | 18  | mΩ   |
|   |                     | V <sub>GS</sub> =2.5V, I <sub>D</sub> =5.5A  | -   | 17   | 24  | mΩ   |
| Forward Transconductance                      | g <sub>FS</sub>     | V <sub>DS</sub> =5V,I <sub>D</sub> =7A   | -   | 20   | -   | S    |
| Dynamic Characteristics <sup>(Note 4)</sup>   |                     |  |     |      |     |      |
| Input Capacitance                             | C <sub>iss</sub>    | V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,<br>F=1.0MHz                                  | -   | 1150 | -   | PF   |
| Output Capacitance                            | C <sub>oss</sub>    |  | -   | 185  | -   | PF   |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>    |  | -   | 145  | -   | PF   |
| Switching Characteristics <sup>(Note 4)</sup> |                     |  |     |      |     |      |
| Turn-on Delay Time                            | t <sub>d(on)</sub>  | V <sub>DD</sub> =10V,R <sub>L</sub> =1.35Ω<br>V <sub>GS</sub> =5V,R <sub>GEN</sub> =3Ω | -   | 6    | -   | nS   |
| Turn-on Rise Time                             | t <sub>r</sub>      |  | -   | 13   | -   | nS   |
| Turn-Off Delay Time                           | t <sub>d(off)</sub> |  | -   | 52   | -   | nS   |
| Turn-Off Fall Time                            | t <sub>f</sub>      |  | -   | 16   | -   | nS   |
| Total Gate Charge                             | Q <sub>g</sub>      | V <sub>DS</sub> =10V,I <sub>D</sub> =7A,<br>V <sub>GS</sub> =4.5V                      | -   | 15   | -   | nC   |
| Gate-Source Charge                            | Q <sub>gs</sub>     |  | -   | 0.8  | -   | nC   |
| Gate-Drain Charge                             | Q <sub>gd</sub>     |  | -   | 3.2  | -   | nC   |
| Drain-Source Diode Characteristics            |                     |  |     |      |     |      |
| Diode Forward Voltage <sup>(Note 3)</sup>     | V <sub>SD</sub>     | V <sub>GS</sub> =0V,I <sub>S</sub> =1A   | -   | -    | 1.2 | V    |
| Diode Forward Current <sup>(Note 2)</sup>     | I <sub>S</sub>      |  | -   | -    | 7   | A    |

Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Surface Mounted on FR4 Board, t ≤ 10 sec.
- ③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- ④ Guaranteed by design, not subject to production

# Typical Electrical and Thermal Characteristics

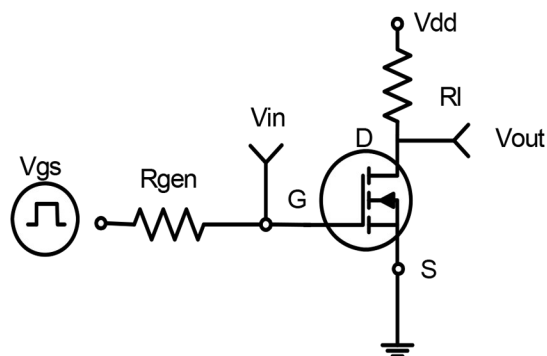


Figure 1 Switching Test Circuit

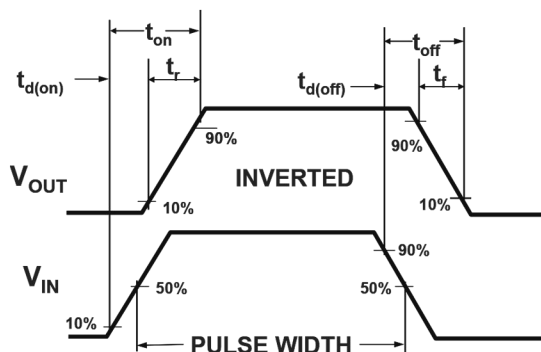
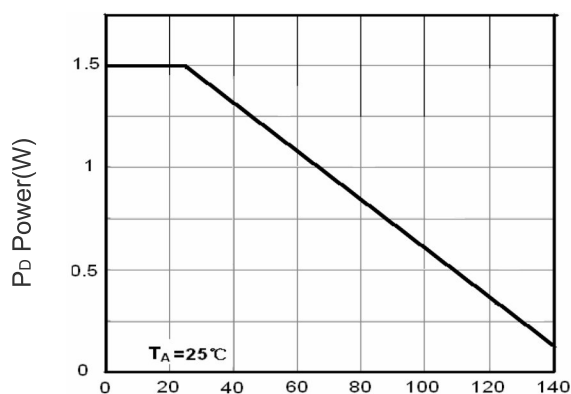
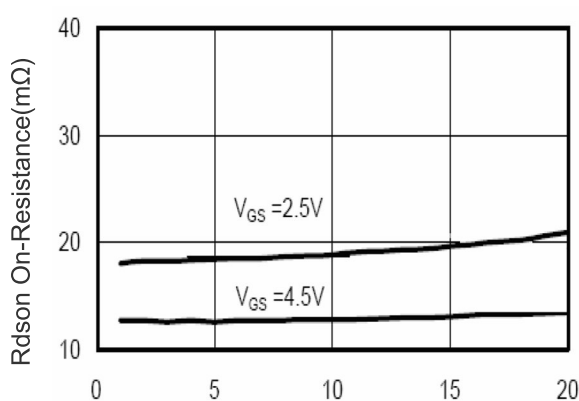


Figure 2 Switching Waveforms



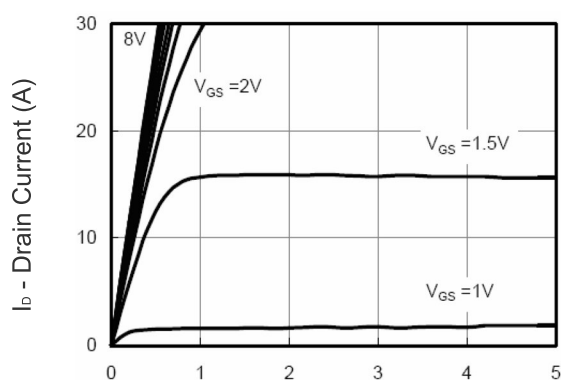
TJ - Junction Temperature(°C)

Figure 3 Power Dissipation



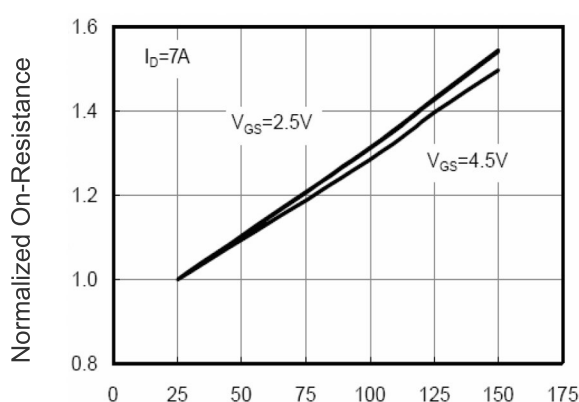
ID - Drain Current (A)

Figure 4 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 5 Output Characteristics



TJ - Junction Temperature(°C)

Figure 6 Drain-Source On-Resistance

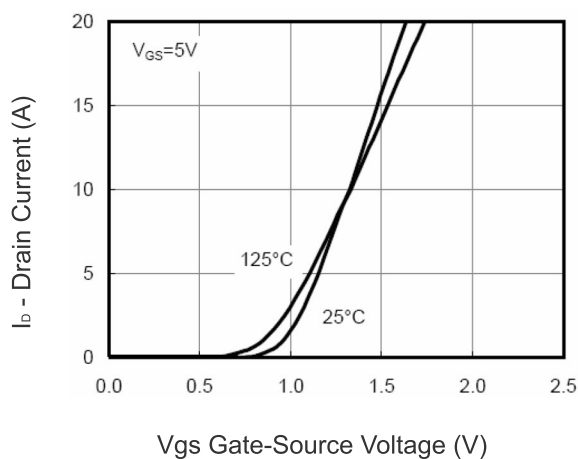


Figure 7 Transfer Characteristics

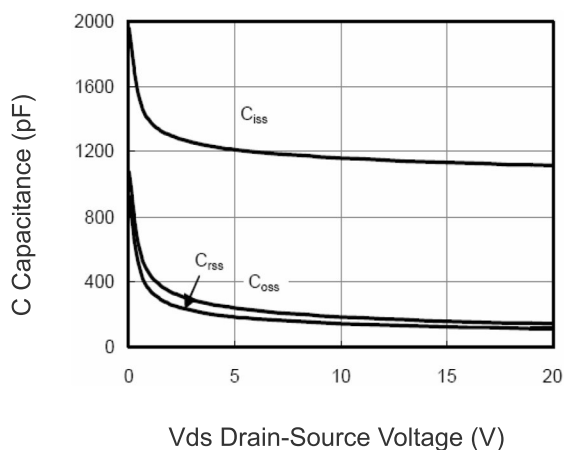
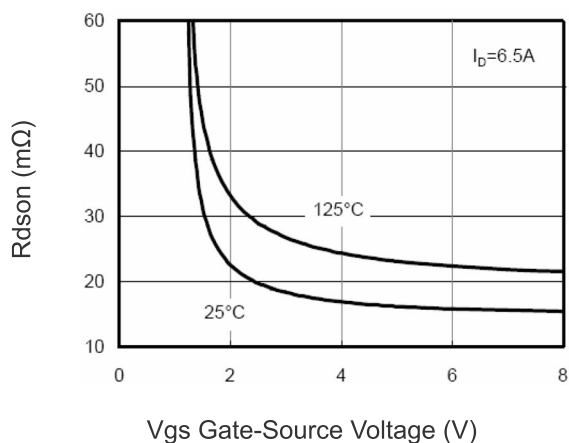
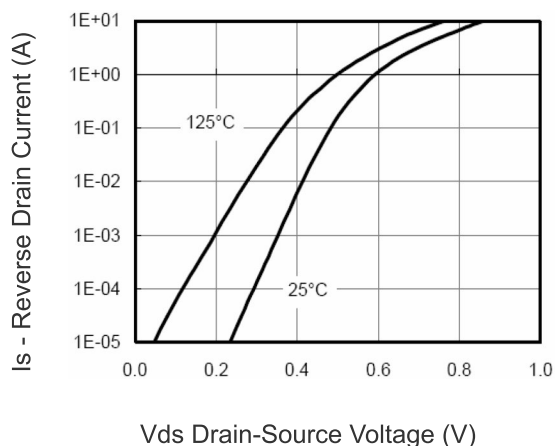
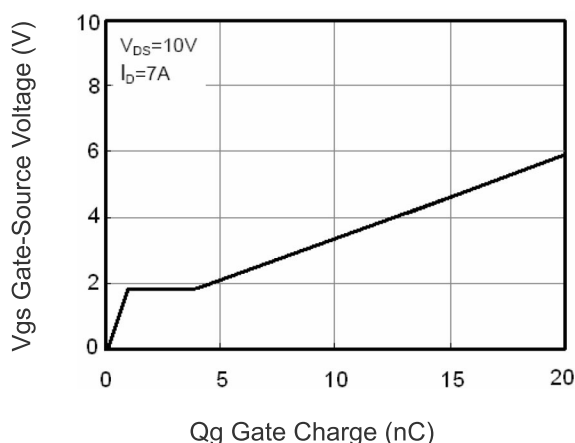

Figure 8 Capacitance vs  $V_{DS}$ 

Figure 9  $R_{DS(on)}$  vs  $V_{GS}$ 

Figure 10 Capacitance vs  $V_{DS}$ 


Figure 11 Gate Charge

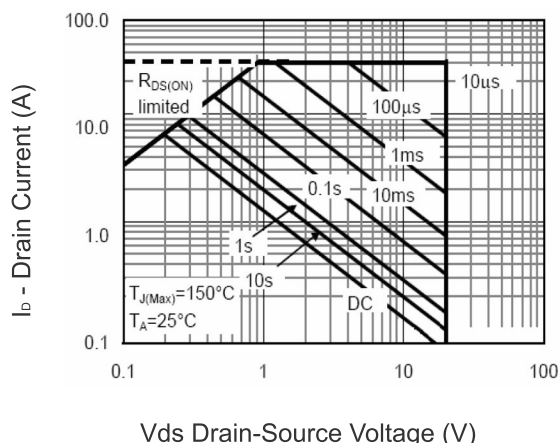


Figure 12 Safe Operation Area

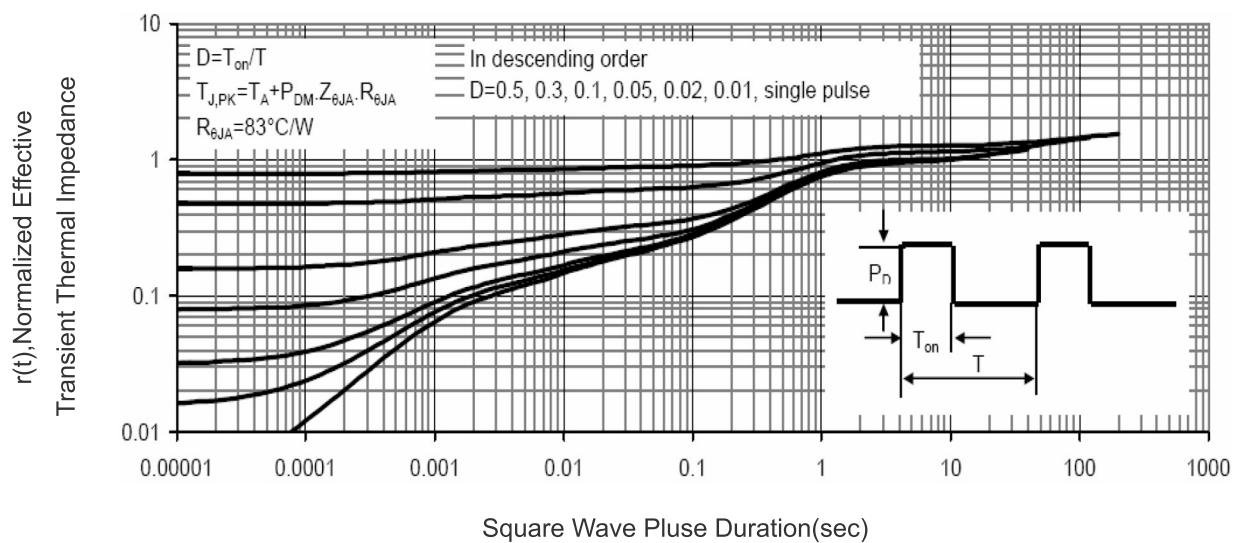
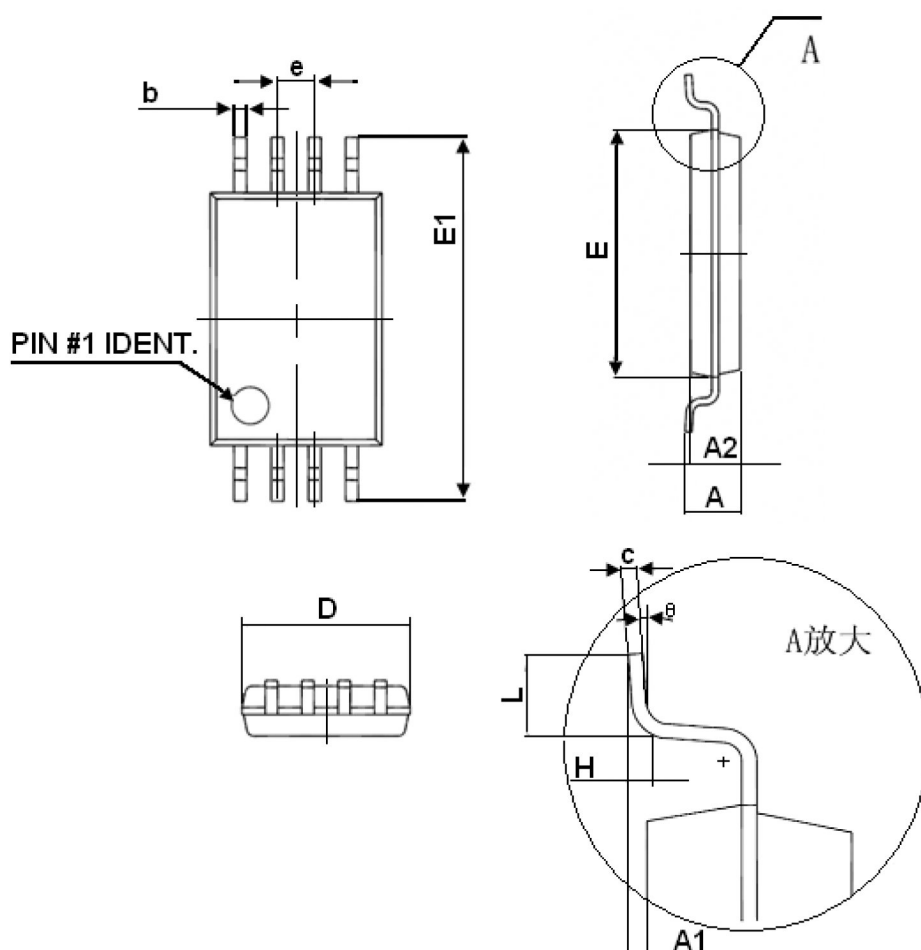


Figure 13 Normalized Maximum Transient Thermal Impedance

## Tssop-8 Package Information



| Symbol | Dimensions In Millimeters |       |
|--------|---------------------------|-------|
|        | Min                       | Max   |
| D      | 2.900                     | 3.100 |
| E      | 4.300                     | 4.500 |
| b      | 0.190                     | 0.300 |
| c      | 0.090                     | 0.200 |
| E1     | 6.250                     | 6.550 |
| A      |                           | 1.100 |
| A2     | 0.800                     | 1.000 |
| A1     | 0.020                     | 0.150 |
| e      | 0.65(BSC)                 |       |
| L      | 0.500                     | 0.700 |
| H      | 0.25(TYP)                 |       |
| θ      | 1°                        | 7°    |

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